

Preliminary datasheet

EconoPIM™3 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 75\text{ A} / I_{CRM} = 150\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Overload operation up to 175°C
 - Low $V_{CE,\text{sat}}$
- Mechanical features
 - High power and thermal cycling capability
 - Integrated NTC temperature sensor
 - Copper base plate
 - Solder contact technology
 - Standard housing
 - Al_2O_3 substrate with low thermal resistance



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

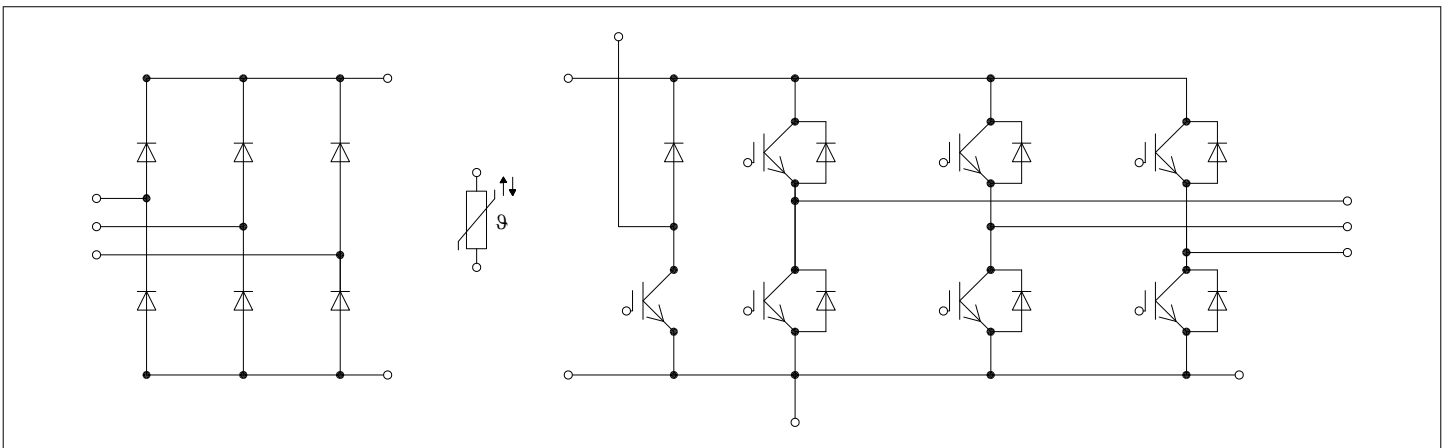


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		>200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$, per switch		2.9		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		3.9		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note		3	6	Nm
Weight	G			300		g

Note: The current under continuous operation is limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 100^\circ\text{C}$	75	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	150	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 75\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	V_{GETh}	$I_C = 1.7\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			1.25		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			2		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			15.1		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.053		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.013	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 75\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 5.6\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.145		μs
			$T_{vj} = 125\ ^\circ C$		0.157		
			$T_{vj} = 175\ ^\circ C$		0.167		
Rise time (inductive load)	t_r	$I_C = 75\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 5.6\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.060		μs
			$T_{vj} = 125\ ^\circ C$		0.064		
			$T_{vj} = 175\ ^\circ C$		0.066		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 75\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.289		μs
			$T_{vj} = 125\ ^\circ C$		0.372		
			$T_{vj} = 175\ ^\circ C$		0.424		
Fall time (inductive load)	t_f	$I_C = 75\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 5.6\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.112		μs
			$T_{vj} = 125\ ^\circ C$		0.216		
			$T_{vj} = 175\ ^\circ C$		0.281		
Turn-on energy loss per pulse	E_{on}	$I_C = 75\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 5.6\ \Omega, di/dt = 910\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		9.09		mJ
			$T_{vj} = 125\ ^\circ C$		11.8		
			$T_{vj} = 175\ ^\circ C$		13.4		
Turn-off energy loss per pulse	E_{off}	$I_C = 75\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 5.6\ \Omega, dv/dt = 3200\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		5		mJ
			$T_{vj} = 125\ ^\circ C$		8.09		
			$T_{vj} = 175\ ^\circ C$		9.74		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		260	A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		250	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.486	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m} \cdot \text{K})$		0.0706		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		75	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	150	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	820	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	630	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 75 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.72	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.59		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.52		
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 75 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 910 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		32	A	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		43		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		50		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_R = 600\text{ V}, I_F = 75\text{ A},$ $V_{GE} = -15\text{ V}, -di_F/dt = 910$ $\text{A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	4.82		μC
			$T_{vj} = 125\text{ }^\circ\text{C}$	10.2		
			$T_{vj} = 175\text{ }^\circ\text{C}$	13.7		
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}, I_F = 75\text{ A},$ $V_{GE} = -15\text{ V}, -di_F/dt = 910$ $\text{A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	1.32		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	3.09		
			$T_{vj} = 175\text{ }^\circ\text{C}$	4.36		
Thermal resistance, junction to case	R_{thJC}	per diode			0.728	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0871		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{op}} > 150\text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ }^\circ\text{C}$	1600	V	
Maximum RMS forward current per chip	I_{FRMSM}	$T_C = 100\text{ }^\circ\text{C}$	95	A	
Maximum RMS current at rectifier output	I_{RMSM}	$T_C = 100\text{ }^\circ\text{C}$	150	A	
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	720	A
			$T_{vj} = 150\text{ }^\circ\text{C}$	565	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2590	A^2s
			$T_{vj} = 150\text{ }^\circ\text{C}$	1600	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 75\text{ A}$		1.00		V
Reverse current	I_r	$T_{vj} = 150\text{ }^\circ\text{C}, V_R = 1600\text{ V}$		1		mA

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			0.602	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$		0.0770		K/W
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj max} = 175 \text{ °C}$ $T_C = 110 \text{ °C}$	50	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj op}$	100	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE sat}$	$I_C = 50 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.50	1.80	V
			$T_{vj} = 125 \text{ °C}$	1.64		
			$T_{vj} = 175 \text{ °C}$	1.72		
Gate threshold voltage	V_{GEth}	$I_C = 1.28 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25 \text{ °C}$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}$		0.92		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25 \text{ °C}$		0		Ω
Input capacitance	C_{ies}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$		11.1		nF
Reverse transfer capacitance	C_{res}	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$		0.039		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}$ $T_{vj} = 25 \text{ °C}$			0.0062	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25 \text{ °C}$			100	nA

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	t_{don}	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 7.5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.052		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.059		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.060		
Rise time (inductive load)	t_r	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 7.5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.060		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.062		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.064		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 7.5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.269		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.365		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.404		
Fall time (inductive load)	t_f	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 7.5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.110		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.207		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.269		
Turn-on energy loss per pulse	E_{on}	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 7.5 \Omega, di/dt = 625 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	5.36		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	6.34		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	6.79		
Turn-off energy loss per pulse	E_{off}	$I_C = 50 \text{ A}, V_{CE} = 600 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 7.5 \Omega, dv/dt = 3045 \text{ V}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	3.41		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	5.36		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	6.57		
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$	190		A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$	180		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.598	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}^*\text{K})$		0.0764		K/W
Temperature under switching conditions	T_{vjop}		-40		175	$^\circ\text{C}$

Note: $T_{vjop} > 150 \text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	1200	V	
Continuous DC forward current	I_F		25	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	50	A	
I^2t - value	I^2t	$t_p = 10\text{ ms}, V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	80	A ² s
			$T_{vj} = 175\text{ °C}$	70	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 25\text{ A}$	$T_{vj} = 25\text{ °C}$	1.83	2.30	V
			$T_{vj} = 125\text{ °C}$	1.70		
			$T_{vj} = 150\text{ °C}$	1.63		
Peak reverse recovery current	I_{RM}	$V_R = 600\text{ V}, I_F = 25\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 685\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	16		A
			$T_{vj} = 125\text{ °C}$	21		
			$T_{vj} = 175\text{ °C}$	23		
Recovered charge	Q_r	$V_R = 600\text{ V}, I_F = 25\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 685\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	1.67		μC
			$T_{vj} = 125\text{ °C}$	3.26		
			$T_{vj} = 175\text{ °C}$	4.23		
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}, I_F = 25\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 685\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	0.54		mJ
			$T_{vj} = 125\text{ °C}$	1.17		
			$T_{vj} = 175\text{ °C}$	1.58		
Thermal resistance, junction to case	R_{thJC}	per diode			1.43	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.182		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}, R_{100} = 493\ \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

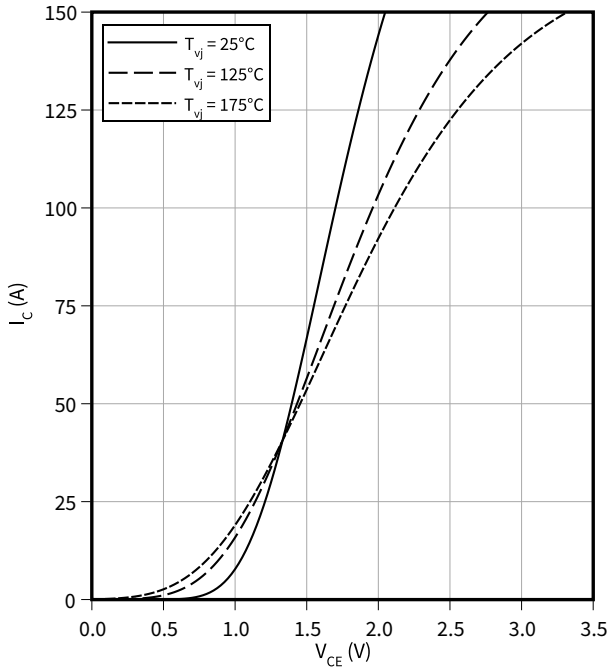
Note: Specification according to the valid application note.

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

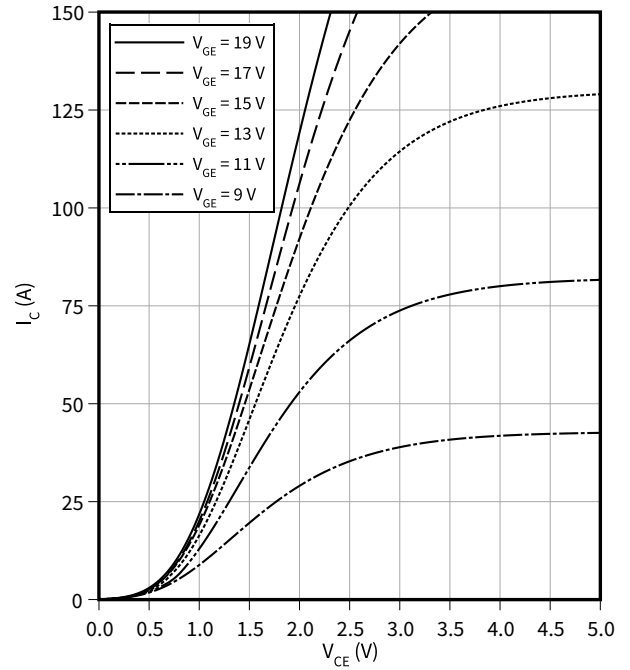
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

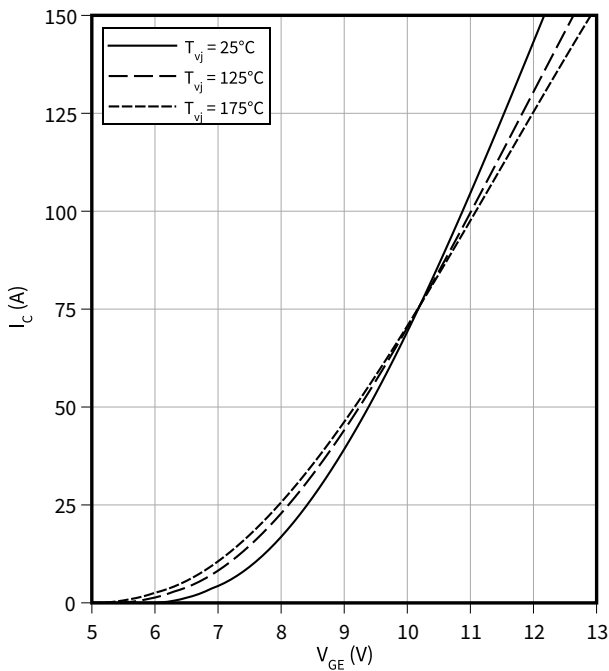
$$T_{vj} = 175 \text{ °C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

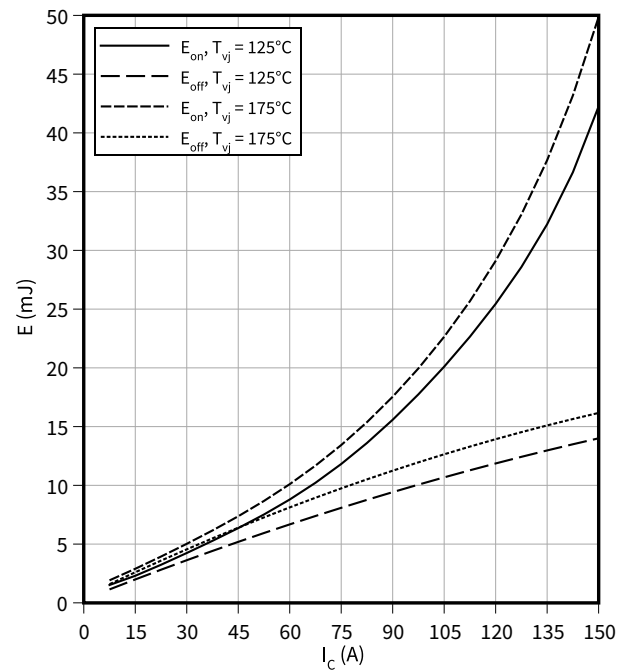
$$V_{CE} = 20 \text{ V}$$



Switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

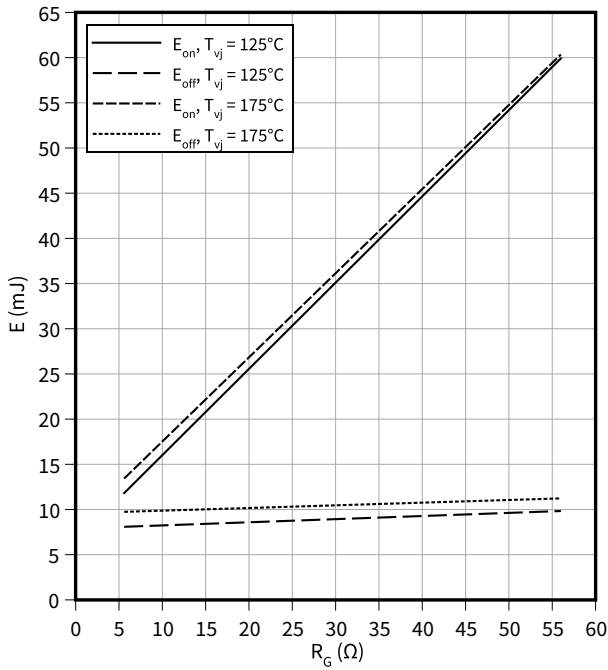
$$R_{Goff} = 5.6 \text{ } \Omega, R_{Gon} = 5.6 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}$$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

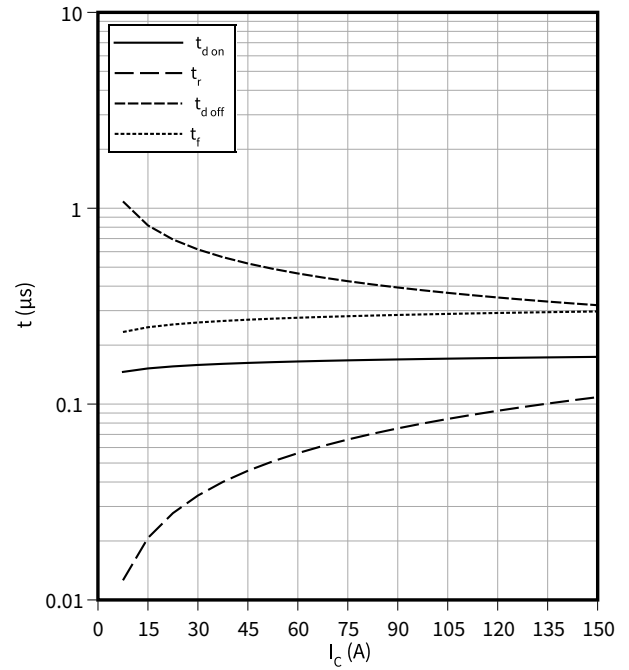
$V_{GE} = \pm 15 \text{ V}$, $I_C = 75 \text{ A}$, $V_{CE} = 600 \text{ V}$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

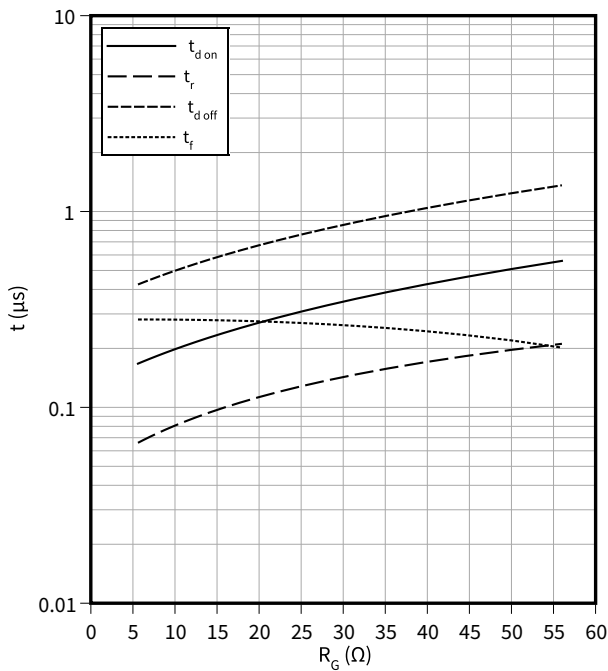
$R_{Goff} = 5.6 \Omega$, $R_{Gon} = 5.6 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 175 \text{ °C}$



Switching times (typical), IGBT, Inverter

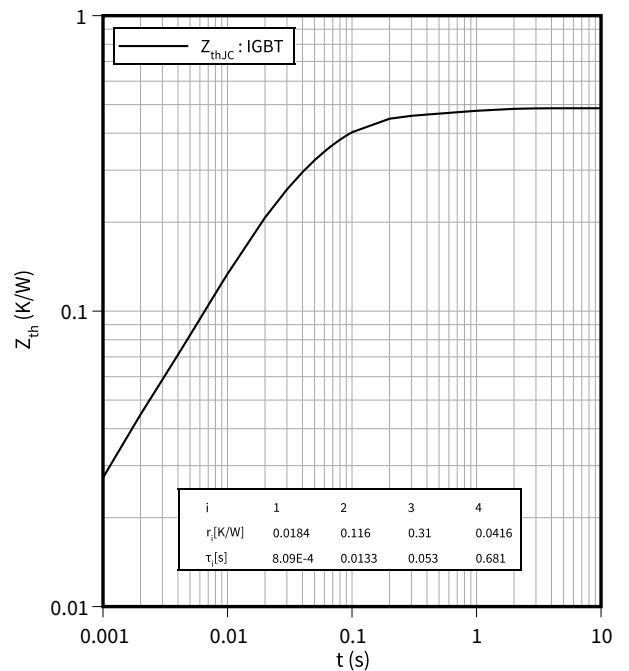
$t = f(R_G)$

$V_{GE} = \pm 15 \text{ V}$, $I_C = 75 \text{ A}$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 175 \text{ °C}$



Transient thermal impedance, IGBT, Inverter

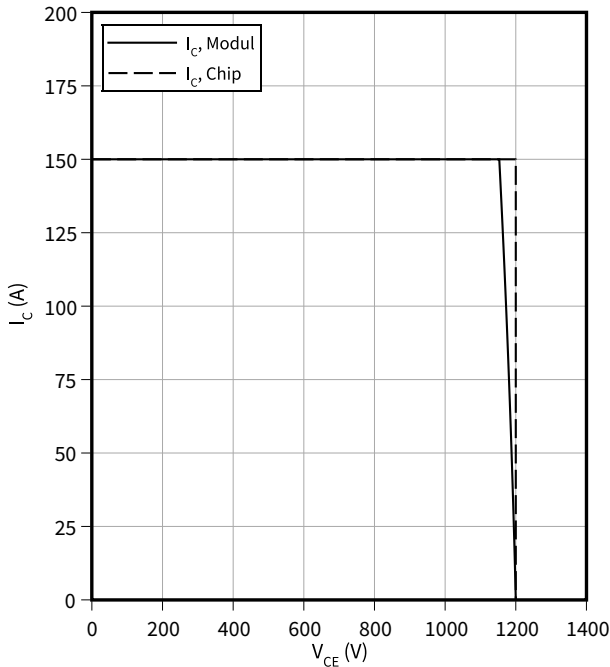
$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

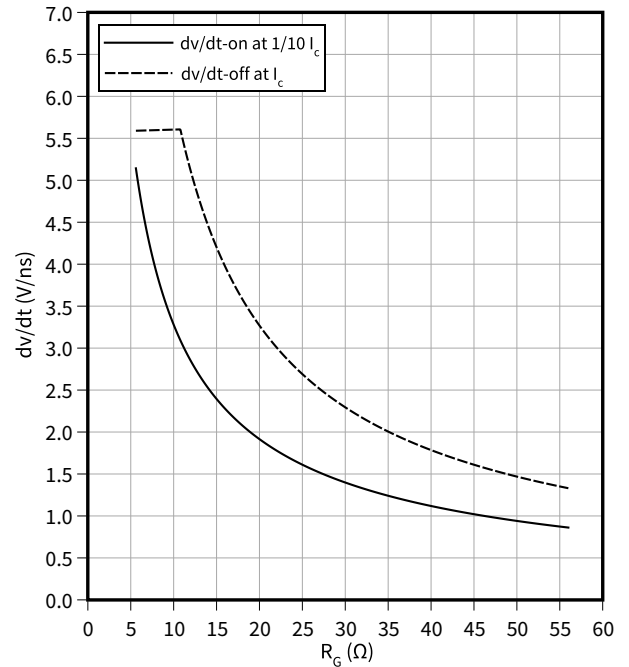
$R_{Goff} = 5.6 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$



Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

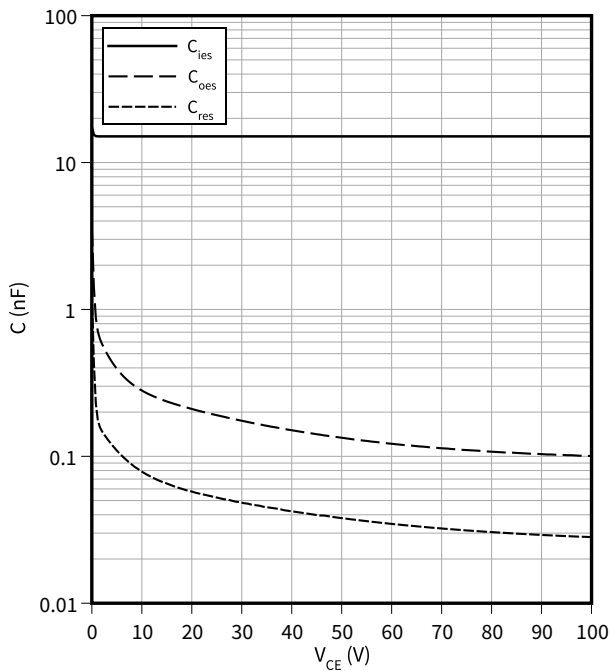
$I_C = 75 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

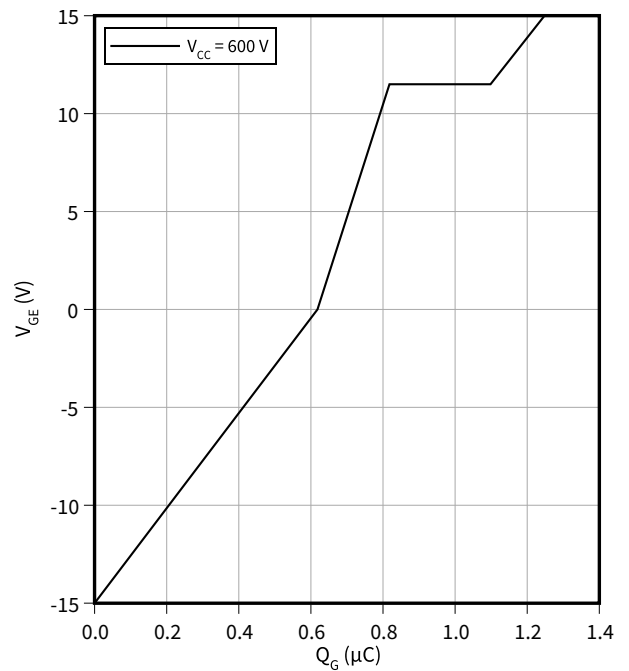
$f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Gate charge characteristic (typical), IGBT, Inverter

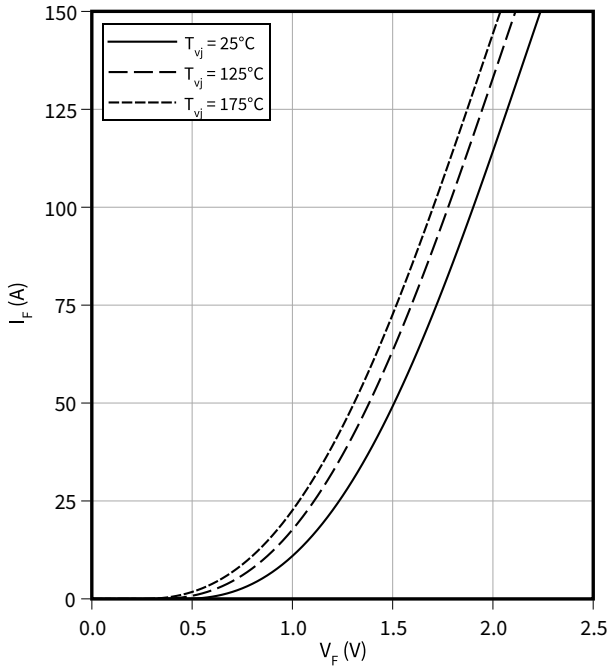
$V_{GE} = f(Q_G)$

$I_C = 75 \text{ A}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Forward characteristic (typical), Diode, Inverter

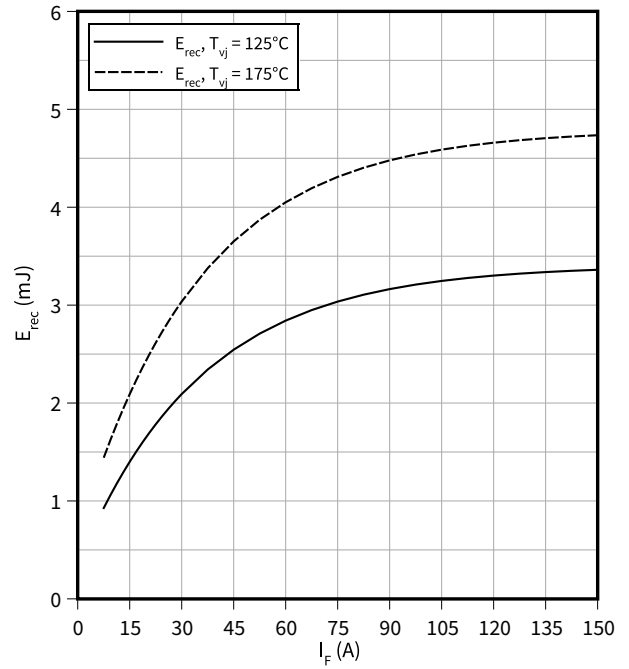
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

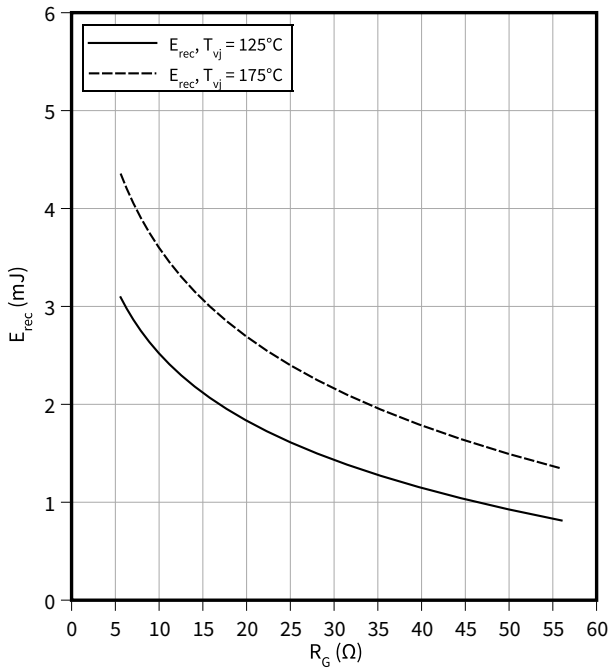
$R_{Gon} = 5.6 \Omega, V_R = 600 \text{ V}$



Switching losses (typical), Diode, Inverter

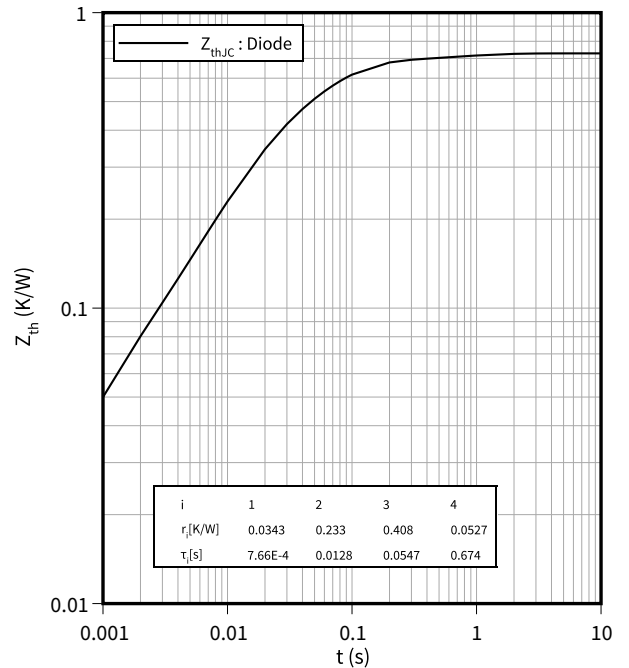
$E_{rec} = f(R_G)$

$I_F = 75 \text{ A}, V_R = 600 \text{ V}$



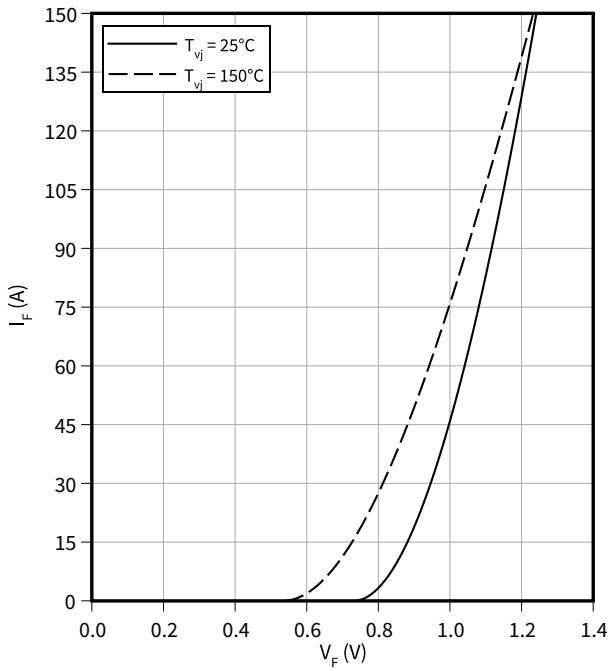
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



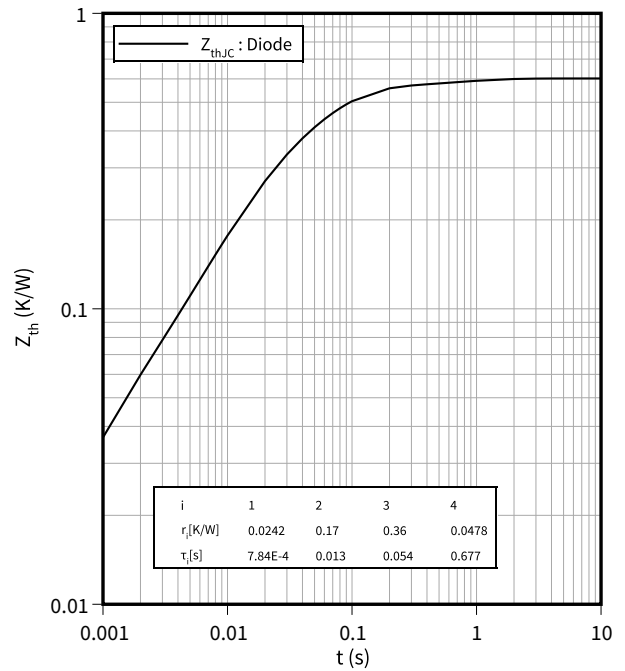
Forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



Transient thermal impedance, Diode, Rectifier

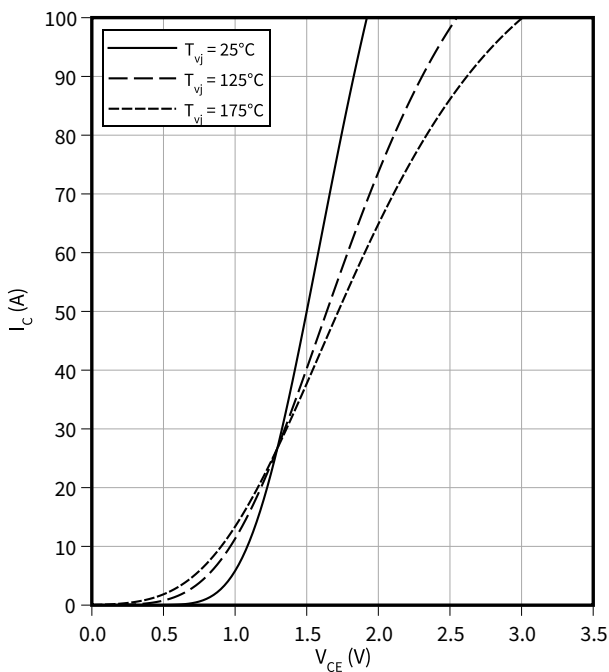
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, Brake-Chopper

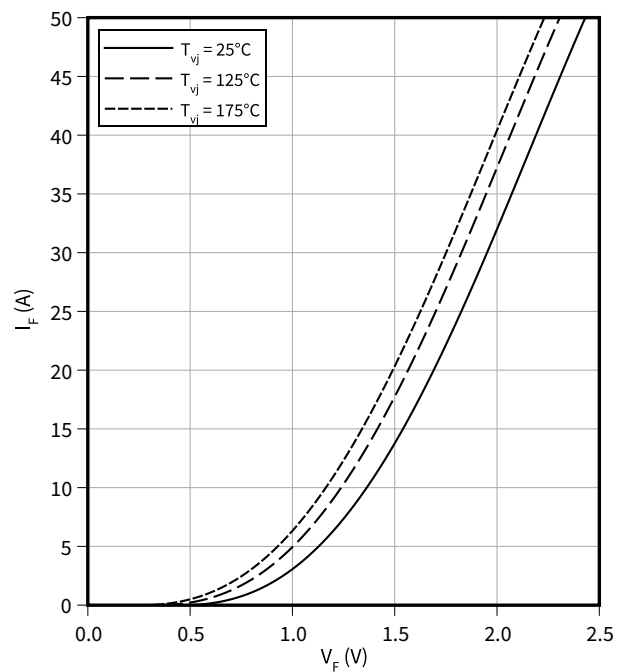
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



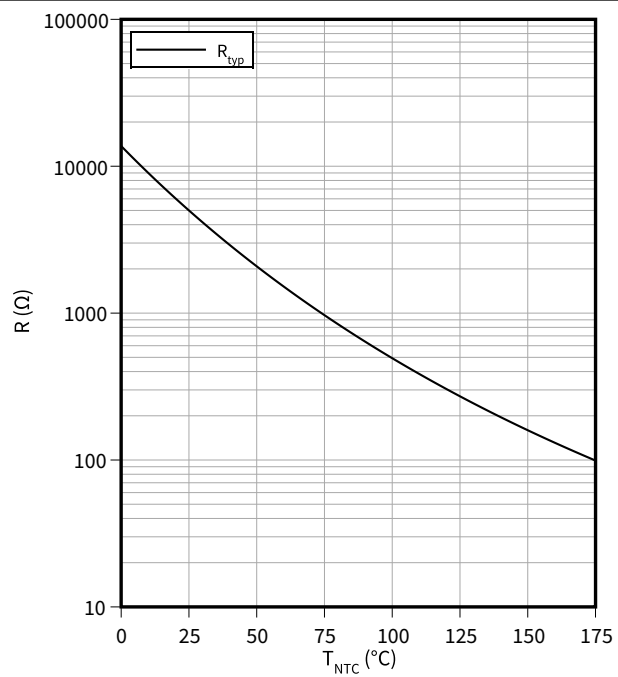
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



9 Circuit diagram

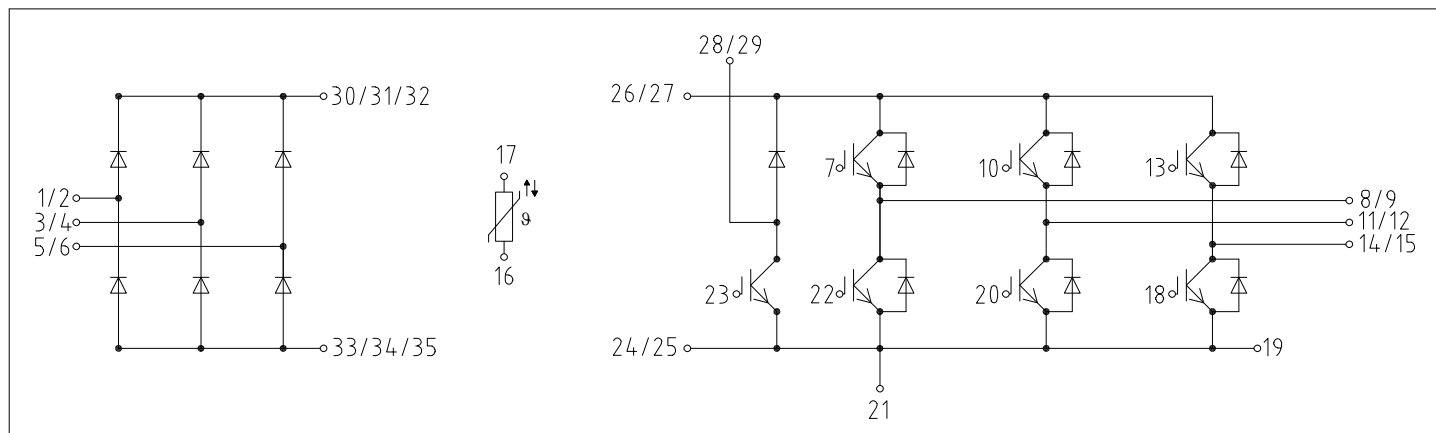


Figure 1

10 Package outlines

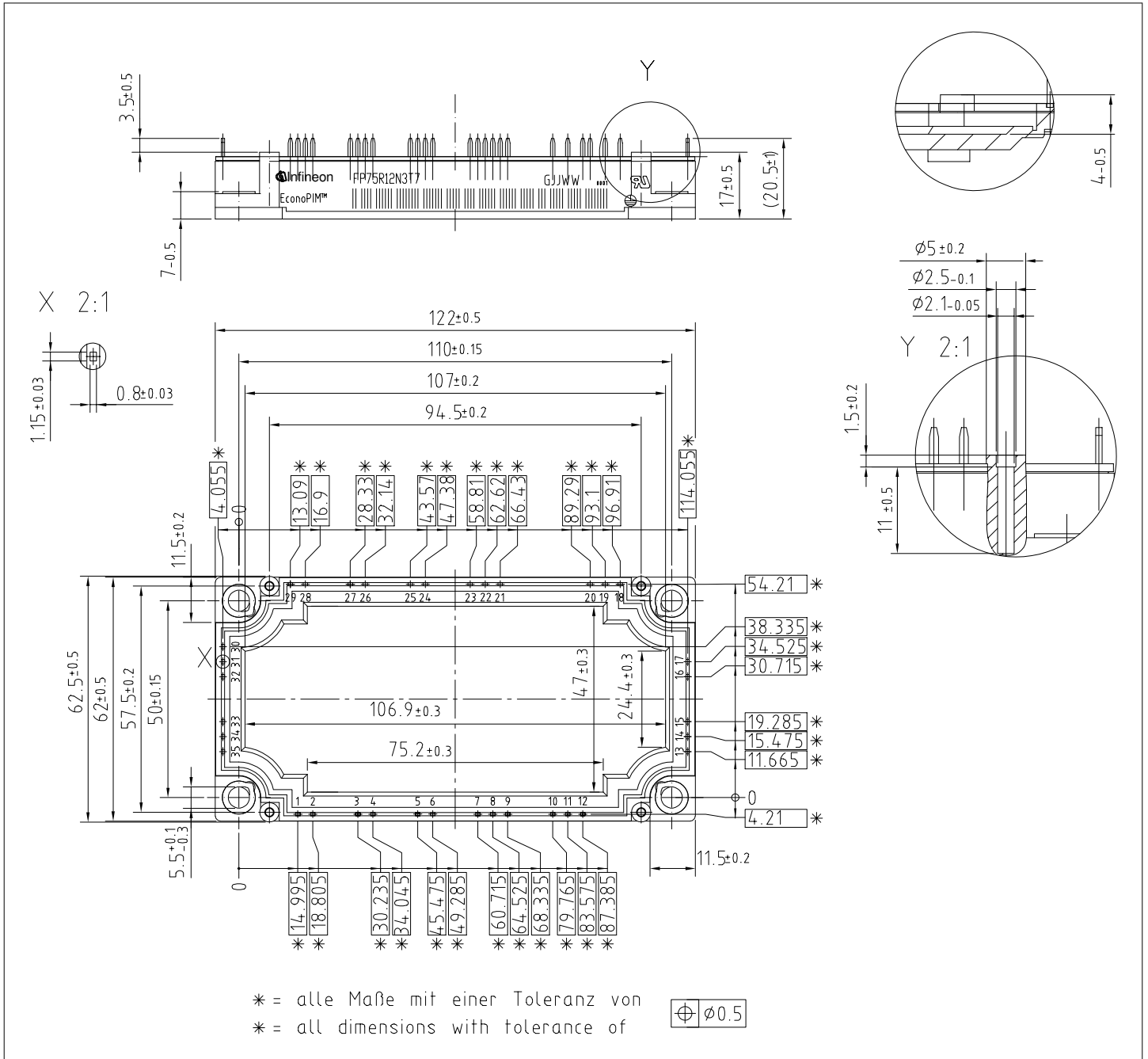


Figure 2

11 Module label code



Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	<i>Example</i> 71549 142846 55054991 15 30
Example	<div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  71549142846550549911530 </div> <div style="text-align: center;">  71549142846550549911530 </div> </div>		

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-12-23	Initial version
0.20	2022-03-02	Preliminary datasheet

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